

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	694	"5837619" "5492843" (adachi and tft)	US-PGP UB; USPAT	OR	OFF	2005/09/29 13:54
L2	28	L1 and step adj coverage	US-PGP UB; USPAT	OR	OFF	2005/09/29 13:54
L3	35553	gate insulating and gate electrode	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/29 13:54
L4	21	L2 and L3	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/29 13:54
L5	7	2 not semiconductor adj energy	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/29 13:55
L6	26	"275638"	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/29 13:56

L7	4	"275638" and adachi	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	ADJ	ON	2005/09/29 13:56
L44	23	(US-20020030228-\$ or US-20020093017-\$ or US-20040126917-\$ or US-20040126938-\$ or US-20040126955-\$ or US-20040127032-\$ or US-20040207015-\$).did. or (US-4414069-\$ or US-4715930-\$ or US-5488005-\$ or US-5605846-\$ or US-5665611-\$ or US-5830787-\$ or US-5834797-\$ or US-5879976-\$ or US-5946561-\$ or US-6004831-\$ or US-6008076-\$ or US-6008078-\$ or US-6124155-\$ or US-6753934-\$ or US-5736414-\$ or US-5747828-\$).did.	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:10
L45	1	("20040207015").PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/09/29 15:15
L46	19	(buffer near conductive) adj film	US-PGP UB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/29 15:49
L47	116	hoon near kim	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49

L48	566	(etch etching etchant etched pattern patterned patterning) near4 buffer and (thin adj film adj transistor or tft)	US-PGP UB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/29 15:49
L49	19	("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904")).PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/09/29 15:49
L50	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGP UB; USPAT; JPO	OR	ON	2005/09/29 15:49
L51	8	(L49 or L50) and (hoon near kim or thin adj film adj transistor or tft)	US-PGP UB; USPAT; JPO	OR	ON	2005/09/29 15:49
L52	231	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	USPAT	OR	ON	2005/09/29 15:49
L53	7359	"117"/\$3.ccls.	USPAT	OR	ON	2005/09/29 15:49
L54	15	L52 and L53	USPAT	OR	ON	2005/09/29 15:49

L55	3550	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49
L56	2969	L55 and step not step adj for	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49
L57	1131	L55 and "257"/\$3.ccls.	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49
L58	6766	(Park-Kee\$ or Yoo-J\$ or Han-M\$).in.	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49
L59	20	(thin adj film adj transistor or tft) and amorphous adj silicon and L58	USPAT	OR	ON	2005/09/29 15:49
L60	121	(thin adj film adj transistor or tft) and amorphous adj silicon and over and etch and (over-etch "over etch")	US-PGP UB; USPAT	OR	ON	2005/09/29 15:49

L61	8094	(257/347,350,390,40,51,57,59,66,72).CCLS.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/09/29 15:49
L62	3615	L61 and (tft thin adj film adj transistor)	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49
L63	926	L62 and buffer	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49
L64	19	(("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904")).PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/09/29 15:49
L65	27990	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49
L66	6766	(Park-Kee\$ or Yoo-J\$ or Han-M\$).in.	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/09/29 15:49

L67	25	"4,767,723"	US-PGP UB; USPAT	OR	ON	2005/09/29 15:49
L68	39	"4851363" not L61	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49
L69	2932	etch adj rate near4 (sin silicon si)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/29 15:49
L70	80	L69 and process near4 etching near4 silicon adj nitride	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/29 15:49
L71	17	"5,310,457"	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/09/29 15:49
L72	694	"5837619" "5492843" (adachi and tft)	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49
L73	26	L1 and step same buffer	US-PGP UB; USPAT	OR	OFF	2005/09/29 15:49

L74	35553	gate insulating and gate electrode	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	ADJ	ON	2005/09/29 15:49
L75	2571	gate insulating with (angstrom or nm or nanometer) and gate electrode with (angstrom or nm or nanometer)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	ADJ	ON	2005/09/29 15:49